

ZXMN10A08G

100V SOT223 N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25 ℃
100V	250mΩ @ V _{GS} = 10V	2.9A
100 V	300mΩ @ V _{GS} = 6V	2.6A

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)

Description

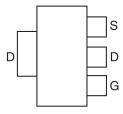
This new generation trench MOSFET from Zetex features a unique structure, combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency, power management applications.

Applications

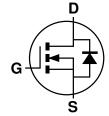
- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control



Top View



Pin Out - Top



Equivalent Circuit

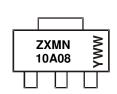
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A08GTA	ZXMN10A08	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



SOT223

ZXMN10A08 = Product Type Marking Code YWW = Date Code Marking Y or Y = Last Digit of Year (ex: 5= 2015) WW or WW = Week Code (01~53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (VGS=10V; TA = +25 °C) (Note 6)		2.9	
(VGS=10V; TA = +70 °C) (Note 6)	I _D	2.3	Α
(VGS=10V; TA = +25 °C) (Note 5)		2.0	
Pulsed Drain Current (Note 7)	I _{DM}	11	А
Continuous Source Current (Body Diode) (Note 6)	Is	5	Α
Pulsed Source Current (Body Diode) (Note 7)	Ism	11	A

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at TA = +25 °C (Note 5) Linear Derating Factor	P _D	2.0 16	W mW/℃
Power Dissipation at TA = +25 °C (Note 6) Linear Derating Factor	P _D	3.9 31	W mW/℃
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	32	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	℃

Electrical Characteristics (@TA = +25 °C, unless otherwise specified.)

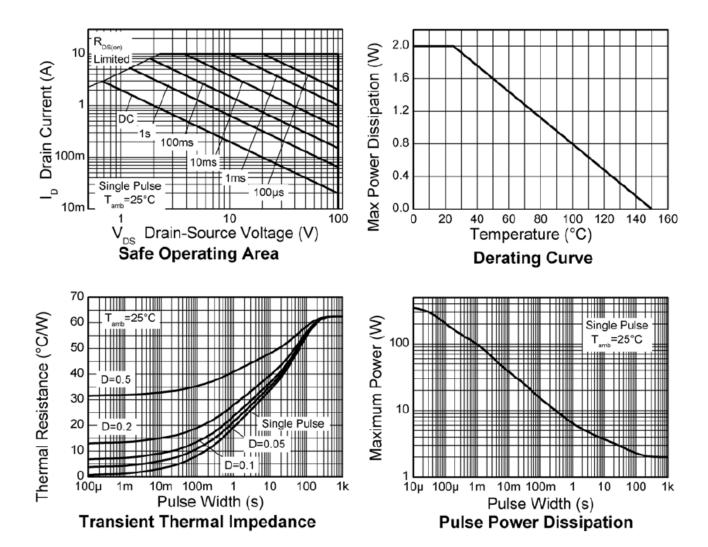
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	100	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	0.5	μΑ	V _{DS} =100V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	-	-	100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS	•		•				
Gate Threshold Voltage	V _{GS(TH)}	2	-	-	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)			-	0.25	Ω	V _{GS} = 10V, I _D = 3.2A	
Static Drain-Source On-Nesistance (Note 6)	R _{DS(ON)}	ı	-	0.30	12	$V_{GS} = 6V, I_D = 2.6A$	
Forward Transconductance (Notes 8 & 10)	g fs	-	5	-	S	V _{DS} = 15V, I _D =3.2A	
Diode Forward Voltage (Note 8)	VsD	-	0.87	0.95	V	TJ=25 °C, Is=3.2A, VGS=0V	
DYNAMIC CHARACTERISTICS (Note 10)		I .		I.			
Input Capacitance	C _{iss}	-	405	-	pF		
Output Capacitance	Coss	-	28.2	-	pF	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	-	14.2	-	pF	1 = 1.0WHZ	
Turn-On Delay Time (Note 9)	t _{D(ON)}	-	3.4	-	ns		
Turn-On Rise Time (Note 9)	t _R	-	2.2	-	ns	$V_{DD} = 30V$, $I_D = 1.2A$, $V_{GS} = 10V$,	
Turn-Off Delay Time (Note 9)	t _{D(OFF)}	-	8	-	ns	$R_G = 6\Omega$	
Turn-Off Fall Time (Note 9)	t _F	-	3.2	-	ns		
Gate Charge (Note 9)	Qg	-	4.2	-	nC	$V_{DS} = 50V$, $V_{GS} = 5V$ $I_{D} = 1.2A$	
Total Gate Charge (Note 9)	Qg	-	7.7	-	nC	V _{DS} = 50V, V _{GS} = 10V I _D = 1.2A	
Gate-Source Charge (Note 9)	Qgs	-	1.8	-	nC		
Gate-Drain Charge (Note 9)	Qgd	-	2.1	-	nC		
Reverse Recovery Time	trr	-	27	-	ns	- TJ=25 °C, IS=1.2A, di/dt= 100A/μs	
Reverse Recovery Charge	Qrr	-	32	-	nC		

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR4 PCB measured at t ≤ 10 secs.
- 7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02, pulse width 300µs pulse width limited by maximum junction temperature.
- 8. Measured under pulsed conditions. Pulse width ${\le}\,300{\mbox{\sc hs}}$. Duty cycle ${\le}\,2\%.$
- 9. Switching characteristics are independent of operating junction temperature.
- 10. For design aid only, not subject to production testing.

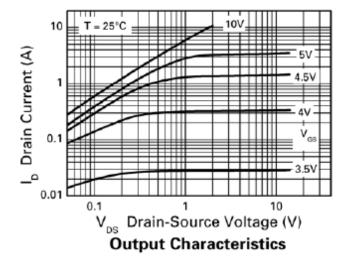


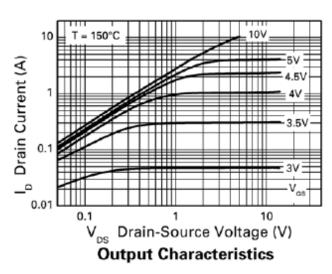
Thermal Characteristics

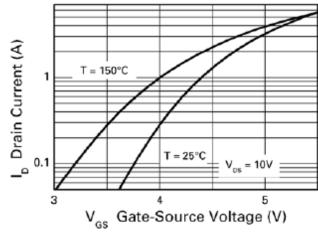


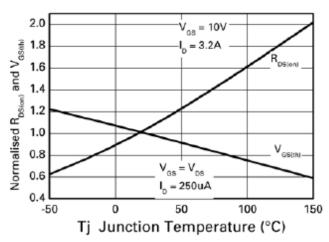


Typical Characteristics

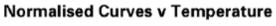


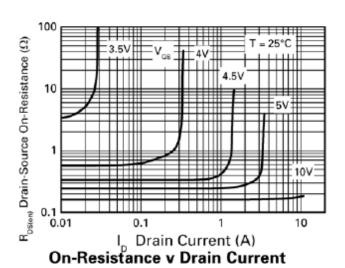


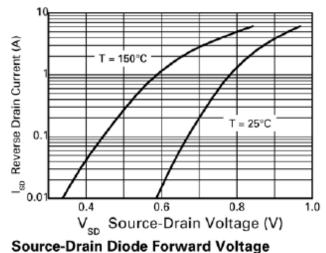




Typical Transfer Characteristics

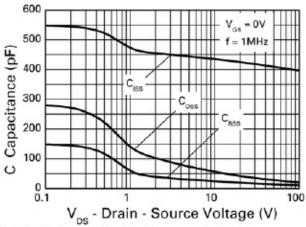






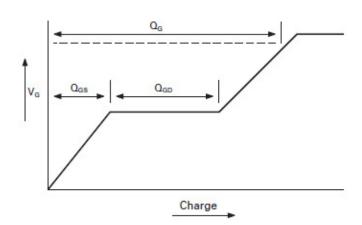


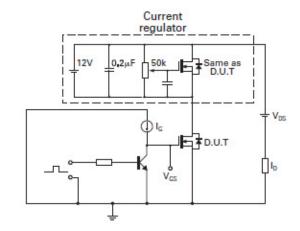
Typical Characteristics (continued)



Capacitance v Drain-Source Voltage

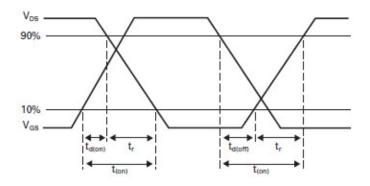
Gate-Source Voltage v Gate Charge

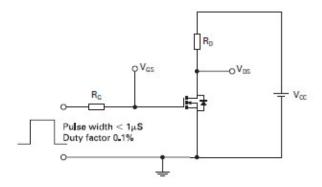




Basic gate charge waveform

Gate charge test circuit





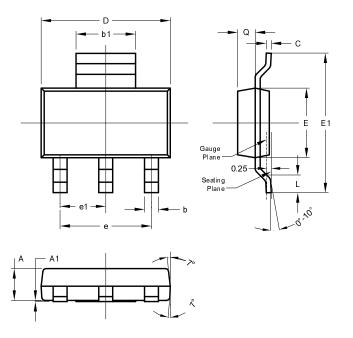
Switching time waveforms

Switching time test circuit



Package Outline Dimensions

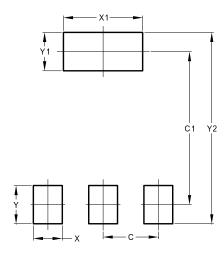
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

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